

# NCD20S15WCT

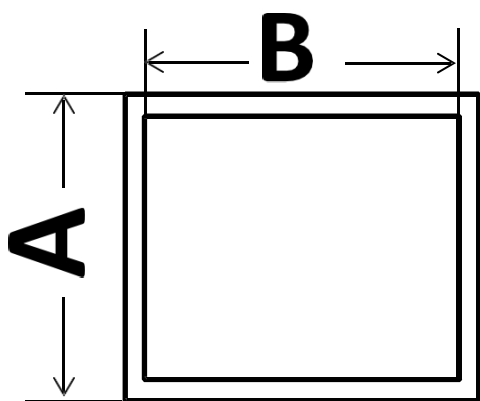
Trench Schottky Barrier Diode Wafer (TSBD)

Maximum Ratings @ $T_A=25^{\circ}\text{C}$  (unless otherwise specified)

Parameter	Symbol	Ratings	Units
Working Peak Reverse Voltage	$V_{RWM}$	200	V
Average Rectified Forward	$I_{F(AV)}$	15	A
Non-repetitive Peak Surge Current (8.3ms, half sine wave) Rated load (JEDEC METHOD)	$I_{FSM}$	220	A
Operating Junction Temperature	$T_J$	175	$^{\circ}\text{C}$

Electrical Characteristics @ $T_A=25^{\circ}\text{C}$

Parameter	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Breakdown Voltage	$V_{BR}$	$I_R=0.05\text{mA}$	200	-	-	V
Forward Voltage Drop	$V_F$	$I_F=10\text{A}$	-	-	0.84	V
		$I_F=15\text{A}$		-	0.89	V
Reverse Leakage Current	$I_R$	$V_R=150\text{V}$	-	-	10	$\mu\text{A}$



Item	Information
Die Size ( A )	2422 $\mu\text{m}$
Top Metal Pad Size (B)	2314 $\mu\text{m}$
Passivation Seal	2352 $\mu\text{m}$
Wafer Thickness	260 $\mu\text{m}$
Gross Die Scribe Line Width	70 $\mu\text{m}$
Top Metal	Al
Back Metal	Ag
Gross Die	2730
Wafer Size	6"